

IN THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application

Listing of Claims:

Claims 1-32 (Cancelled)

33. (Previously Presented) A solid-state imaging apparatus being one of pieces diced from an assembly, the solid-state imaging apparatus comprising:

a light-receiving chip having a plurality of light-receiving cells arranged either one dimensionally or two dimensionally on one main surface of a base substrate, the main surface being made up of a light-receiving area on which the light-receiving cells are arranged and a periphery area surrounding the light-receiving area; and

a transparent protection plate, at least a part thereof that corresponds to the light-receiving area being transparent, wherein

the transparent protection plate has a skirt portion at a periphery thereof,

the skirt portion is positioned on the periphery area of the main surface thereby forming a space between the light-receiving cells and the transparent protection plate, and

the assembly is comprised of two layers, the two layers being a sheet of transparent protection plates and a semiconductor wafer of light-receiving chips that are attached to each other such that each transparent protection plate is combined with a corresponding light-receiving chip, and the diced pieces have such diced edges that result by cutting the two layers simultaneously.

34. (Previously Presented) The solid-state imaging apparatus of Claim 33, wherein the skirt portion is formed by plating metal on the periphery of the transparent protection plate that is a flat plate made of glass or resin.

35. (Previously Presented) The solid-state imaging apparatus of Claim 33, wherein the transparent protection plate is a flat plate made of resin, and the skirt portion is formed by pressing the flat resin plate.

36. (Previously Presented) A solid-state imaging apparatus being one of pieces diced from an assembly, the solid-state imaging apparatus comprising:

a light-receiving chip having a plurality of light-receiving cells arranged either one dimensionally or two dimensionally on one main surface of a base substrate, the main surface being made up of a light-receiving area on which the light-receiving cells are arranged and a periphery area surrounding the light-receiving area; and

a transparent protection plate, at least a part thereof that corresponds to the light-receiving area being transparent, wherein

the light-receiving chip has, on the periphery area of the main surface, a rib portion having a loop shape,

the rib portion is attached onto a periphery of the transparent protection plate thereby forming a space between the light-receiving cells and the transparent protection plate, and

the assembly is comprised of two layers, the two layers being a sheet of transparent protection plates and a semiconductor wafer of light-receiving chips that are attached to each other such that each transparent protection plate is combined with a corresponding light-receiving chip, and the diced pieces have such diced edges that result by cutting the two layers simultaneously.

37. (Previously Presented) The solid-state imaging apparatus of Claim 36, wherein the rib portion is an insulator made of a material for protective foil.

38. (Previously Presented) A solid-state imaging apparatus being one of pieces diced from an assembly, the solid-state imaging apparatus comprising:

a light-receiving chip having a plurality of light-receiving cells arranged either one dimensionally or two dimensionally on one main surface of a base substrate, the main surface being made up of a) a light-receiving area positioned in a central portion of the main surface, the light-receiving cells being arranged on the light-receiving area, and b) a periphery area surrounding the light-receiving area, a plurality of electrodes being provided outside the light-receiving area; and

a transparent protection plate, at least a part thereof that corresponds to the light-receiving area being transparent, wherein

the transparent protection plate includes: a plurality of terminal pads formed on the other main surface that is different from the main surface,

a plurality of holes are provided through the transparent protection plate, each hole electrically connecting one of the electrodes with a corresponding one of the terminal pads, and

the assembly is comprised of two layers, the two layers being a sheet of transparent protection plates and a semiconductor wafer of light-receiving chips that are attached to each other such that each transparent protection plate is combined with a corresponding light-receiving chip, and the diced pieces have such diced edges that result by cutting the two layers simultaneously.

39. (Previously Presented) The solid-state imaging apparatus of Claim 38, wherein a plurality of holes are provided through the translucent protection plate, and conductive foil is attached to a side wall of each of the holes.

40. (Previously Presented) The solid-state imaging apparatus of Claim 38, wherein a plurality of holes are provided through the translucent protection plate, and each of the holes is filled with a conductive material.

41. (Previously Presented) A solid-state imaging apparatus comprising:
a light-receiving chip having a plurality of light-receiving cells arranged either one dimensionally or two dimensionally on one main surface of a base substrate, the main surface being made up of a) a light-receiving area positioned in a central portion of the main surface, the light-receiving cells being arranged on the light-receiving area, and b) a periphery area surrounding the light-receiving area, a plurality of electrodes being provided outside the light-receiving area; and

a transparent protection plate, at least a part thereof that corresponds to the light-receiving area being transparent, wherein

the transparent protection plate includes: a plurality of terminal pads formed on the other main surface that is different from the main surface; and a plurality of conductive foils that are insulated from each other, each conductive foil electrically connecting one of the electrodes with

a corresponding one of the terminal pads, and being attached to the main surface, a corresponding side surface, and the other main surface of the transparent protection plate.

42. (Previously Presented) The solid-state imaging apparatus of Claim 36, wherein the rib portion is produced on the periphery area of the main surface, by a semiconductor producing process.

43. (New) The solid-state imaging apparatus of Claim 33, wherein the skirt portion is formed of a sealing material.

44. (New) The solid-state imaging apparatus of Claim 43, further comprising a collective lens of the light-receiving cell, wherein the thickness of a space between the transparent protection plate and the light-receiving cells is greater than a height of the collective lens by $10\ \mu\text{m} - 100\ \mu\text{m}$.

45. (New) The solid-state imaging apparatus of Claim 43, further comprising a collective lens of the light-receiving cell, wherein a space between the transparent protection plate and the light-receiving cells is filled with a resin whose refractive index is smaller than that of the collective lens.